## **EAST Search History**

|          |      | •   |  |                     |         |                  |
|----------|------|---|--|---------------------|---------|------------------|
| Ref<br># | Hits | Search Query  | DBs  | Default<br>Operator | Plurals | Time Stamp       |
| S86      | 5480 | (metal adj oxide or HfSiO or ZrSiO or "ZrO.sub.2" or "HfSiO.sub.2" or "HfO. sub.2" or hafnium adj oxide or zirconium adj oxide) with gate adj (dielectric or isolat\$4 or insulat\$4) | US-PGPUB;<br>USPAT;<br>USOCR;<br>FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2007/04/12 16:02 |
| S87      | 4903 | transistor and S86  | US-PGPUB;<br>USPAT;<br>USOCR;<br>FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2007/04/12 16:02 |
| S88      | 4817 | semiconductor and S87   | US-PGPUB;<br>USPAT;<br>USOCR;<br>FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2007/04/12 16:03 |
| S89      | 1459 | @ad<="20040426" and S85   | US-PGPUB;<br>USPAT;<br>USOCR;<br>FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2007/04/12 16:04 |